

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicant : Powell, et al.
Serial No. : 10/080,119
Filed : February 21, 2002
Title : METHOD OF FORMING A DIELECTRIC LAYER
Docket : MIO 0060 VA (98-0814.01)
Examiner : D. Le
Art Unit : 2818

Assistant Commissioner for Patents
Washington, DC 20231

CERTIFICATE OF FACSIMILE TRANSMISSION
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Sir:

AMENDMENT

This paper is being filed in response to the office action mailed on October 8, 2002. Reconsideration is respectfully requested in light of the amendments and remarks below.

CLEAN VERSION OF THE AMENDMENTS

(A version of the amendments showing the markings is provided in a separate appendix attached to this paper.)

In the Specification

At page 1, line 1, the title should read:

--"METHOD OF FORMING A DIELECTRIC LAYER"--

At page 25, the Abstract should read:

"Methods for fabricating a dielectric layer are provided. In one embodiment, a silicon-containing material is deposited on a substrate. The deposited material is processed with a reactive agent to react with silicon atoms of the deposited material to form the dielectric layer. The silicon-containing dielectric layer can allow for improved